PFP4N70E / PFF4N70E

650V N-Channel MOSFET

FEATURES

- Originative New Design
- 100% EAS Test
- Rugged Gate Oxide Technology
- Extremely Low Intrinsic Capacitances
- Remarkable Switching Characteristics
- Unequalled Gate Charge : 10 nC (Typ.)
- Extended Safe Operating Area
- Lower $R_{DS(ON)}$: 2.45 Ω (Typ.) @V_{GS}=10V
- Halogen Free

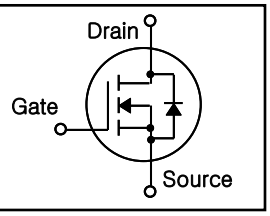
APPLICATION

- Low power battery chargers
- Switch mode power supply (SMPS)
- DC-AC converters.

BV_{DSS} = 700 V

$R_{DS(on)}$ = 2.45 Ω

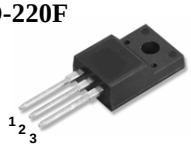
I_D = 4.0 A



TO-220

1.Gate 2. Drain 3. Source

TO-220F



1.Gate 2. Drain 3. Source

Absolute Maximum Ratings

T_C=25℃ unless otherwise specified

Symbol	Parameter		PFP4N70E	PFF4N70E	Units
V_{DSS}	Drain-Source Voltage		700		V
I_D	Drain Current – Continuous (T_C = 25℃)		4.0	4.0*	A
	Drain Current – Continuous (T_C = 100℃)		2.6	2.6*	A
I_{DM}	Drain Current – Pulsed	(Note 1)	16.1	16.1*	A
V_{GS}	Gate-Source Voltage		±30		V
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	240		mJ
I_{AR}	Avalanche Current	(Note 1)	4.0		A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	10.0		mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	5.5		V/ns
P_D	Power Dissipation (T_C = 25℃)		100	33	W
	- Derate above 25℃		0.80	0.26	W/℃
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150		℃
T_L	Maximum lead temperature for soldering purposes, 1/8” from case for 5 seconds		300		℃

Thermal Resistance Characteristics

Symbol	Parameter	PFP4N70E	PFF4N70E	Units
$R_{\theta JC}$	Junction-to-Case	1.25	3.79	℃/W
$R_{\theta JA}$	Junction-to-Ambient	62.5	62.5	

* When mounted on the minimum pad size recommended (PCB Mount)

Electrical Characteristics T_C=25 °C unless otherwise specified

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
On Characteristics						
V_{GS}	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 uA	2.5	--	4.5	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 2.0 A	--	2.45	2.8	Ω
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 uA	700	--	--	V
ΔBV_{DSS} /ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250 uA, Referenced to25℃	--	0.6	--	V/℃
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 700 V, V_{GS} = 0 V	--	--	10	uA
		V_{DS} = 560 V, T_C = 125℃	--	--	100	uA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 30 V, V_{DS} = 0 V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -30 V, V_{DS} = 0 V	--	--	-100	nA
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz	--	585	760	pF
C_{oss}	Output Capacitance		--	63	82	pF
C_{rss}	Reverse Transfer Capacitance		--	4	6	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Time	V_{DS} = 350 V, I_D = 4.0 A, R_G = 25 Ω (Note 4,5)	--	14	28	ns
t_r	Turn-On Rise Time		--	7.5	15	ns
$t_{d(off)}$	Turn-Off Delay Time		--	28	56	ns
t_f	Turn-Off Fall Time		--	6.5	13	ns
Q_g	Total Gate Charge	V_{DS} = 560 V, I_D = 4.0 A, V_{GS} = 10 V (Note 4,5)	--	10	15	nC
Q_{gs}	Gate-Source Charge		--	3.2	--	nC
Q_{gd}	Gate-Drain Charge		--	3.8	--	nC
Source-Drain Diode Maximum Ratings and Characteristics						
I_S	Continuous Source-Drain Diode Forward Current		--	--	4.0	A
I_{SM}	Pulsed Source-Drain Diode Forward Current		--	--	16.1	A
V_{SD}	Source-Drain Diode Forward Voltage	I_S = 4.0 A, V_{GS} = 0 V	--	--	1.5	V
trr	Reverse Recovery Time	I_S = 4.0 A, V_{GS} = 0 V, di_F/dt = 100 A/μs (Note 4)	--	290	--	ns
Qrr	Reverse Recovery Charge		--	1.8	--	μC

Notes ;

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. I_{AS}=4.0A, V_{DD}=50V, R_G=25Ω, Starting T_J=25°C
3. I_{SD}≤4.0A, di/dt≤300A/μs, V_{DD}≤BV_{DSS} , Starting T_J=25 °C
4. Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2%
5. Essentially Independent of Operating Temperature

Typical Characteristics

Fig 1. Output Characteristics

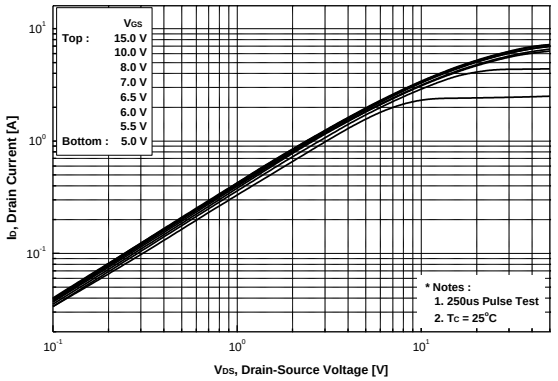


Fig 2. Transfer Characteristics

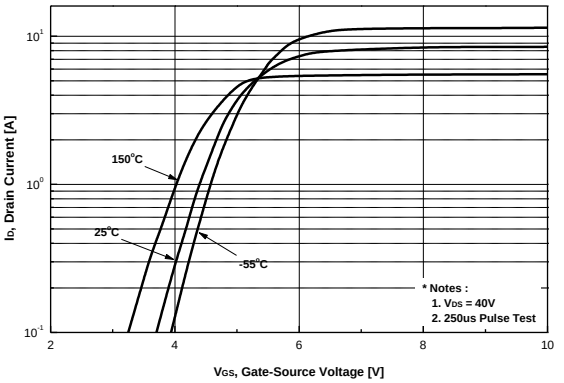


Fig 3. Static Drain-Source On Resistance

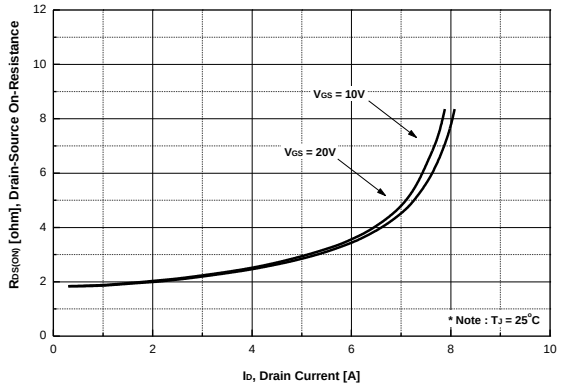


Fig 4. Source-Drain Diode Forward Voltage

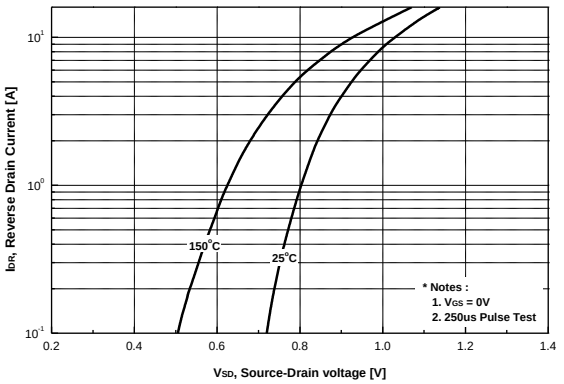


Fig 5. Capacitance Characteristics

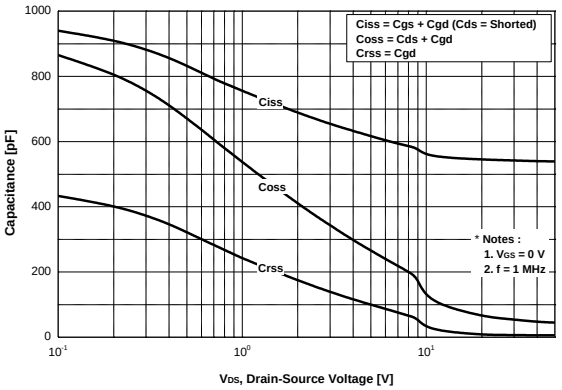


Fig 6. Gate Charge Characteristics

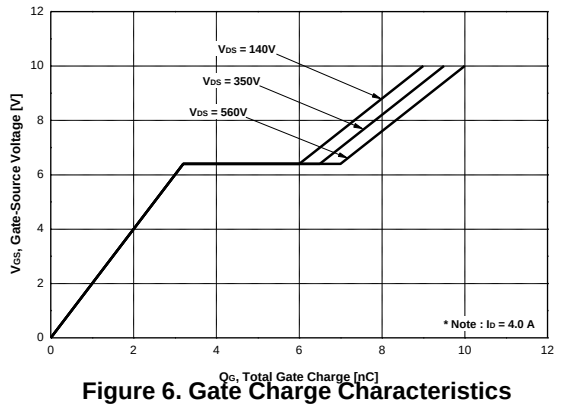


Figure 6. Gate Charge Characteristics

Typical Characteristics

Fig 7. BV_{DSS} vs. Junction Temperature

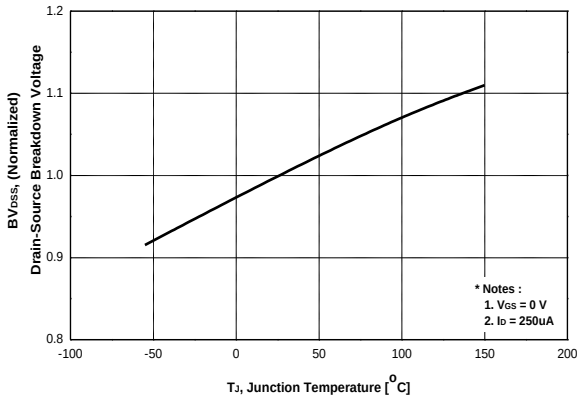


Fig 8. $R_{DS(ON)}$ vs. Junction Temperature

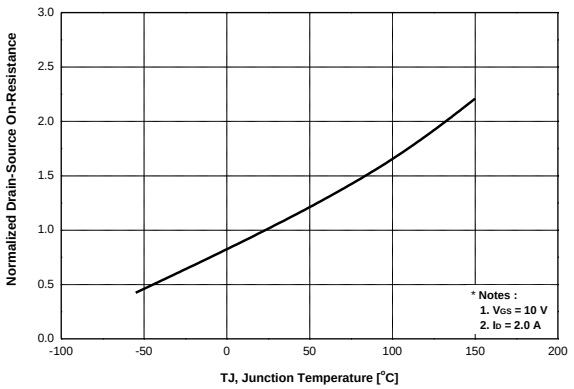


Fig 3. Static Drain-Source On Resistance

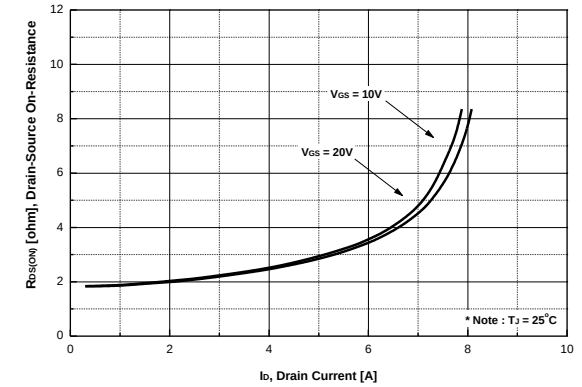


Fig 4. Source-Drain Diode Forward Voltage

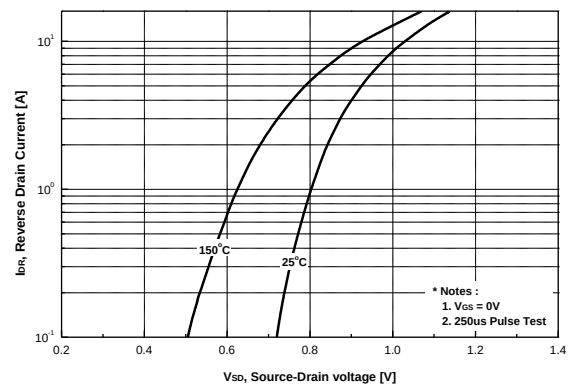


Fig 5. Capacitance Characteristics

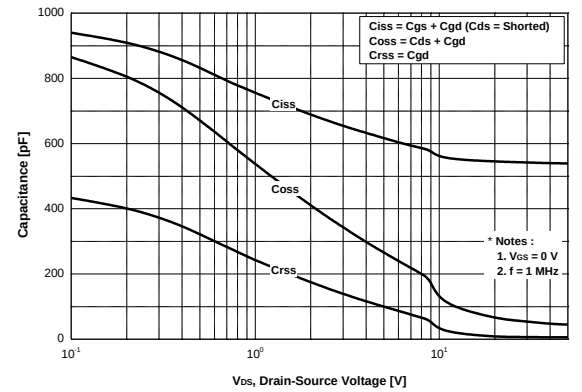


Fig 6. Gate Charge Characteristics

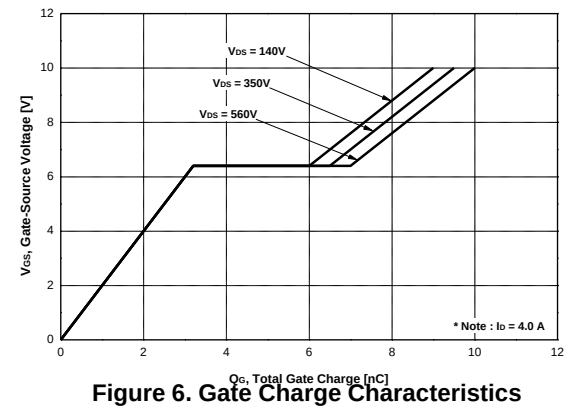
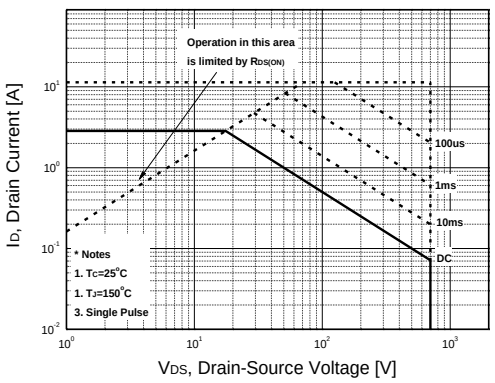


Figure 6. Gate Charge Characteristics

Typical Characteristics (continued)

Figure 7. Breakdown Voltage Variation vs Temperature

Figure 8. On-Resistance Variation vs Temperature



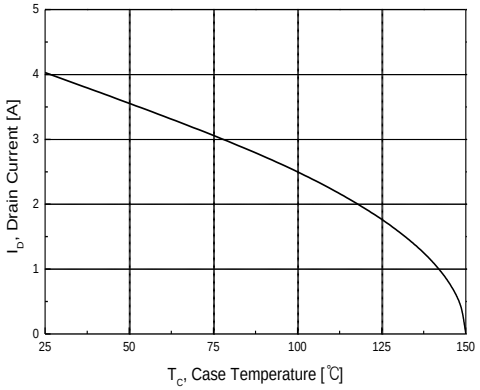


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs Case Temperature

Figure 11. Transient Thermal Response Curve

Characteristics Test Circuit & Waveform

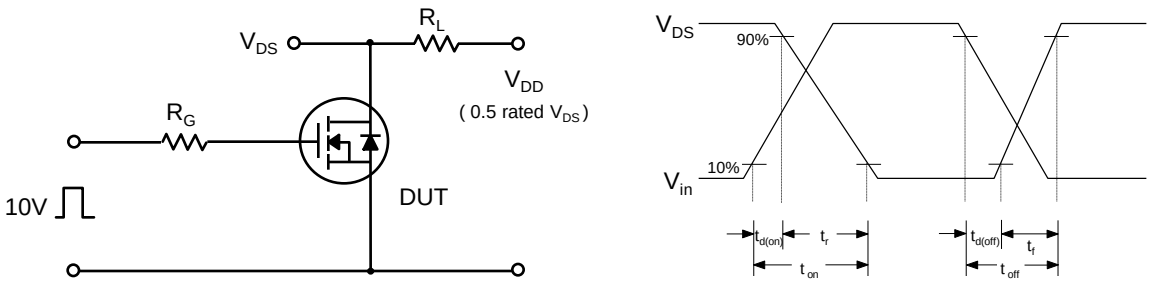


Fig 14. Resistive Switching Test Circuit & Waveforms

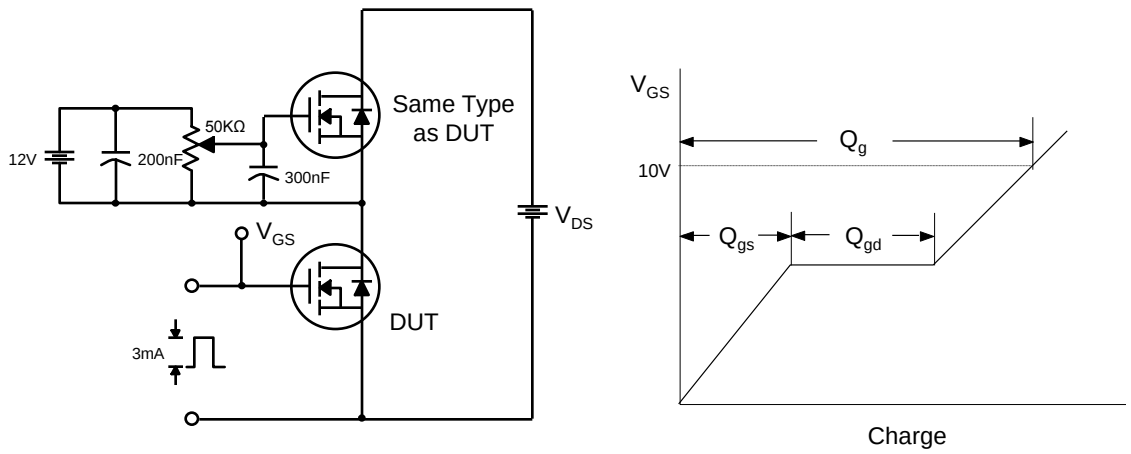


Fig 15. Gate Charge Test Circuit & Waveform

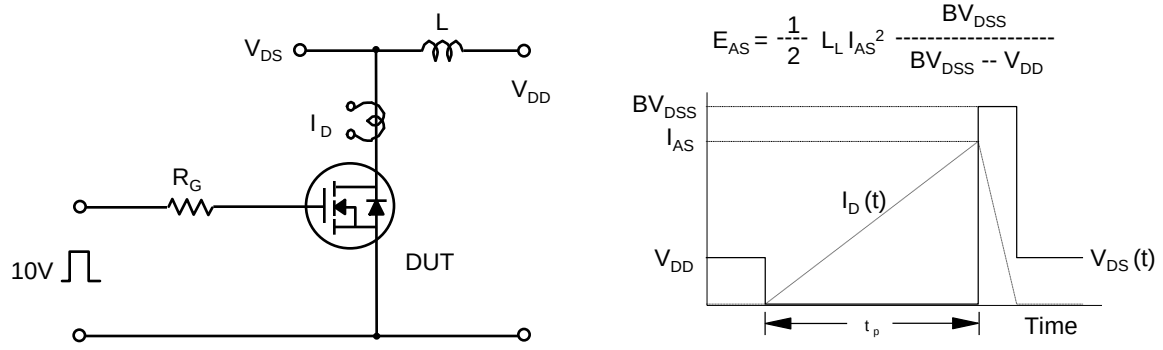
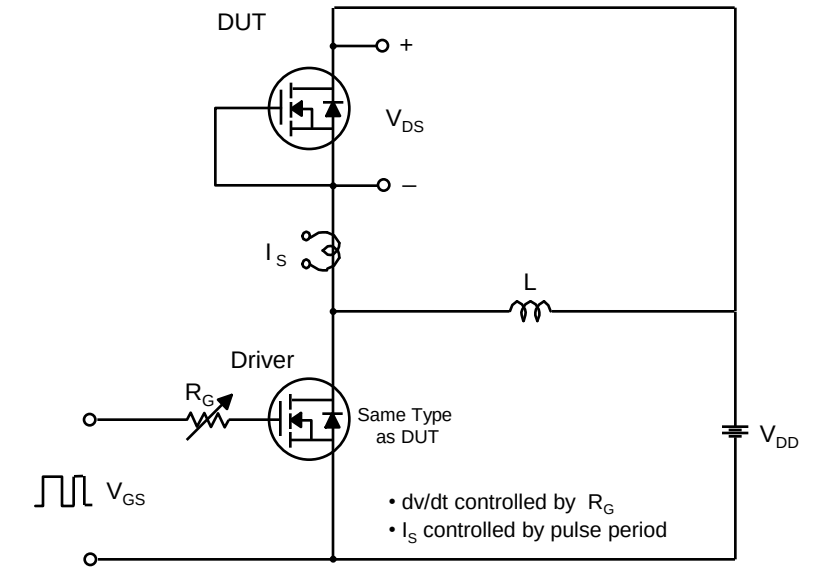


Fig 16. Unclamped Inductive Switching Test Circuit & Waveforms

Characteristics Test Circuit & Waveform (continued)



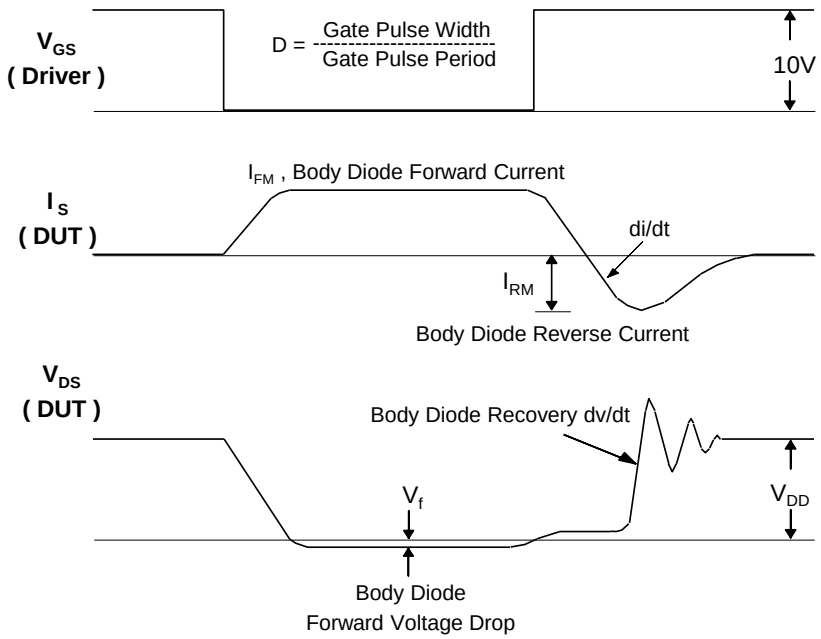
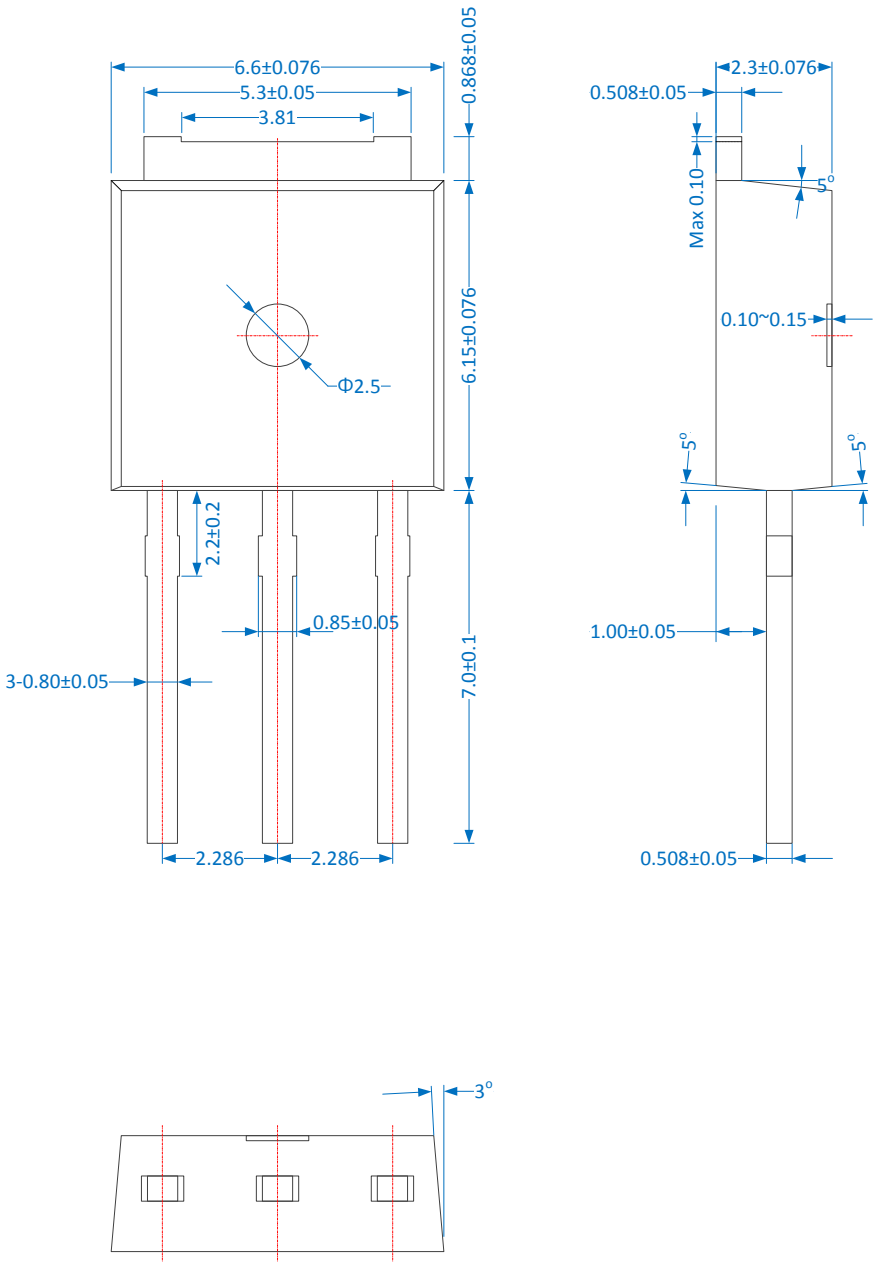


Fig 17. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Package Dimension

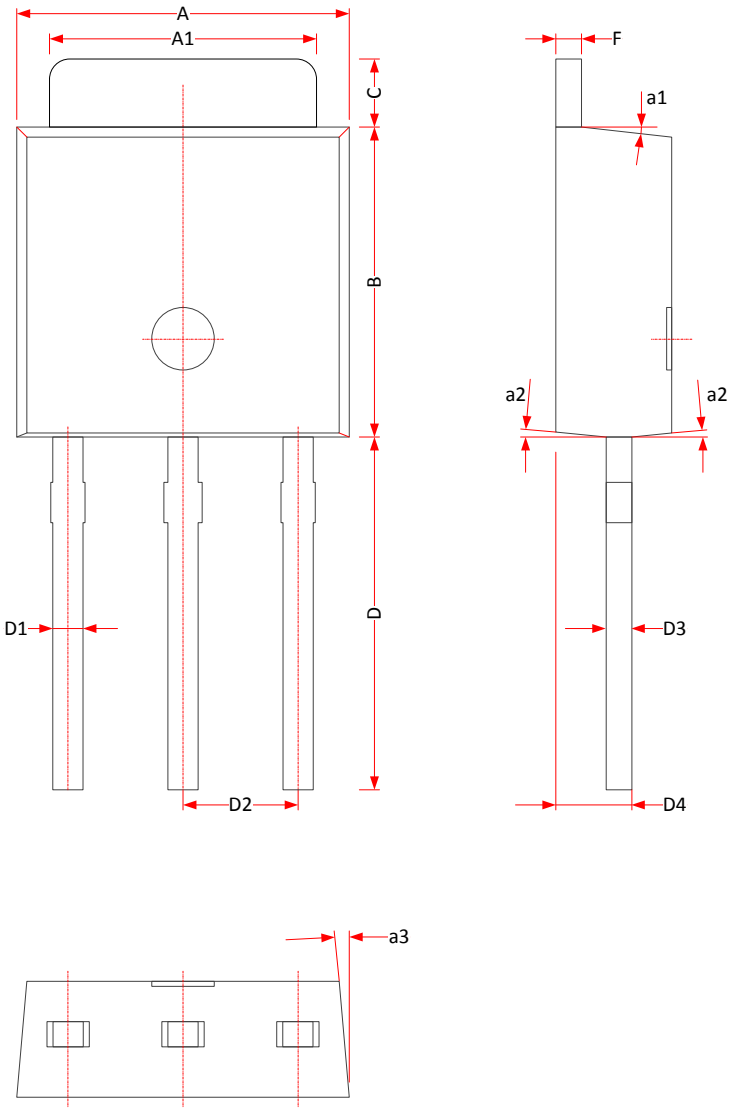
I-PAK(TO-251) ⓩ



Package Dimension

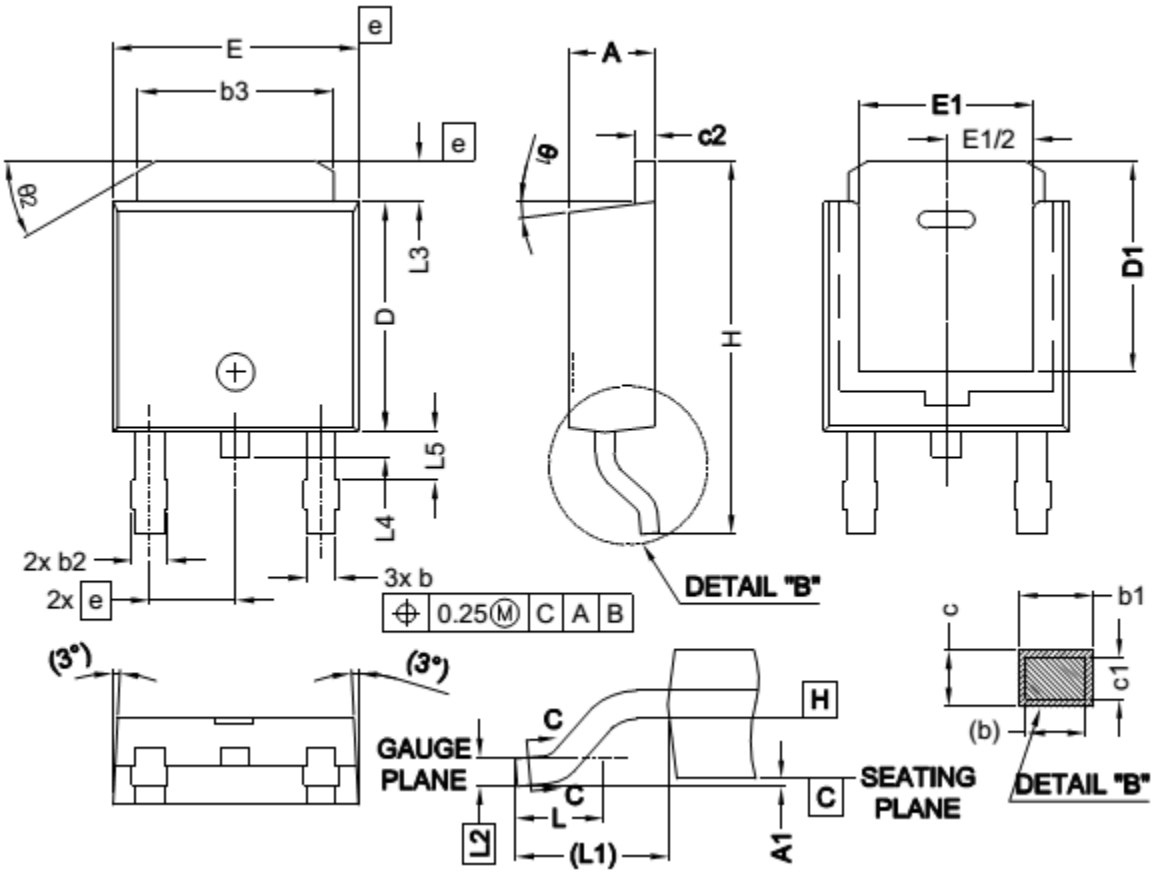
I-PAK(TO-251) ⓗ

Symbol	Millimeters
A	6.40 ~ 6.60
A1	5.30 ~ 5.50
B	5.40 ~ 5.70
C	1.35 ~ 1.65
D	7.40 ~ 8.00
D1	0.60 ~ 0.75
D2	2.30
D3	0.49 ~ 0.59
D4	1.72 ~ 1.82
E	2.20 ~ 2.40
F	0.55 ~ 0.65
a1	5 deg
a2	5 deg
a3	2 deg



Package Dimension

D-PAK(TO-252) ⓐ



SYMBOL	MIN.	MAX.	SYMBOL	MIN.	MAX.	SYMBOL	MIN.	MAX.
A	2.18	2.39	E	6.35	6.73	φ1	0°	15°
A1	-	0.13	E1	4.32	-	φ2	25°	35°
b	0.640	0.884	e	2.29 BSC				
b1	0.65	0.79	H	9.94	10.34			
b2	0.760	1.124	L	1.50	1.78			
b3	4.95	5.46	L1	2.74 REF				
c	0.46	0.61	L2	0.51 BSC				
c1	0.41	0.56	L3	0.89	1.27			
c2	0.40	0.60	L4	-	1.02			
D	5.97	6.22	L5	1.140	1.492			
D1	5.21	-	φ	0°	10°			

Package Dimension

D-PAK(TO-252) ⓩ